	Application No.	Applicant(s)		
Notice of Allowability	10/614,368	YAGISHITA ET AL.		
	Examiner	Art Unit		
	Bradley K Smith	2824		
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	ppears on the cover should be cover should be covered by the cover should be covered by the cove	SED in this application. If not includ communication will be mailed in due	ed course. <b>THIS</b>	
1. $\boxtimes$ This communication is responsive to <u>2/24/04</u> .				
2. ⊠ The allowed claim(s) is/are <u>1 and 2</u> .				
3. $igotimes$ The drawings filed on <u>08 July 2003</u> are accepted by the	Examiner.			
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority</li> <li>a)  All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents have</li> </ul>		a)-(d) or (f).		
<ol><li>Certified copies of the priority documents had</li></ol>	ave been received in App	olication No. <u>09/609,106</u> .		
3.  Copies of the certified copies of the priority	documents have been re	eceived in this national stage applica	tion from the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
Applicant has THREE MONTHS FROM THE "MAILING DATI noted below. Failure to timely comply will result in ABANDOI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.			quirements	
5. A SUBSTITUTE OATH OR DECLARATION must be sub- INFORMAL PATENT APPLICATION (PTO-152) which g			OTICE OF	
6. CORRECTED DRAWINGS ( as "replacement sheets") n	nust be submitted.			
(a) ☐ including changes required by the Notice of Draftsp	erson's Patent Drawing I	Review ( PTO-948) attached		
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date	·			
(b) ☐ including changes required by the attached Examine Paper No./Mail Date	er's Amendment / Comm	nent or in the Office action of		
Identifying indicia such as the application number (see 37 CFF each sheet. Replacement sheet(s) should be labeled as such i			e back) of	
<ol> <li>DEPOSIT OF and/or INFORMATION about the de attached Examiner's comment regarding REQUIREMEN</li> </ol>			Note the	
Address to the second of the s				
Attachment(s) 1. ⊠ Notice of References Cited (PTO-892)	5. ☐ Notice	e of Informal Patent Application (PT	O-152)	
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948	B) 6. ☐ Interv	6. ☐ Interview Summary (PTO-413),		
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/St Paper No./Mail Date 7/8/03</li> </ol>		Paper No./Mail Date 7. ⊠ Examiner's Amendment/Comment		
4. ☐ Examiner's Comment Regarding Requirement for Deposi	t 8. 🛭 Exam	iner's Statement of Reasons for Allo	owance	
of Biological Material 9. ⊠ Other <u>Search notes</u> .				
I.I.S. Potent and Trademark Office.	Company of the compan	RICHARD ELMS SUPERVISORY PATENT E) TECHNOLOGY CENTER		

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

Notice of Allowability

Part of Paper No./Mail Date 20040319

## **DETAILED ACTION**

## Election/Restrictions

1. This application is in condition for allowance except for the presence of claims 3 to 9 non-elected without traverse. Accordingly, claims 3-9 have been cancelled.

## **EXAMINER'S AMENDMENT**

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows: cancel claims 3-9

In the cross reference add -- This application is a division of 09/609109 now US Patent 6,607,952. --

Delete the ablstract and replace with:

- A semiconductor device with a source and drain formed in a semiconductor substrate; a crystallized gate insulating film formed on the substrate in a region between the source semiconductor and drain; gate electrode formed on the gate insulating and film; an insulating film formed on a side surface of the gate electrode and having an amorphous structure formed from the same material as that of the gate insulating film. Furthermore the insulating film is essentially formed from a material selected from the group consisting of cerium oxide (CeO<sub>2</sub>), zirconium oxide (ZrO<sub>2</sub>), hafnium oxide (HfO<sub>2</sub>), thorium oxide (ThO<sub>2</sub>), yttrium oxide (Ya<sub>2</sub>O<sub>3</sub>), calcium fluoride (CaF<sub>2</sub>), tin-calcium fluoride (CaSnF<sub>2</sub>), titanium-barium oxide (BaTiO<sub>2</sub>), and La<sub>2</sub>O<sub>3</sub>. - -

3. The following is an examiner's statement of reasons for allowance: the prior art of

record neither teaches nor suggests the formation of a crystallized gate insulating film,

and an amorphous insulating film formed from the same material on the side surface of

the gate.

Statement of Reasons for Allowance."

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on

Conclusion

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Tsunashima et al. (US Patent 6,376,888) disclose a dielectric material around the gate electrode but fail to disclose an amorphous dielectric on the side of the gate electrode. Kamata et al. (US Pre Grant Publication No. 2002/0063299) disclose a crystalline gate dielectric layer but fail to disclose an amorphous dielectric on the side of the gate electrode. Ami et al. (US Pre Grant Publication No. 2003/0136331) disclose a method of forming cerium oxide.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Bradley K Smith whose telephone number is (571)272-1884. The examiner can normally be reached on 10-6 Monday through Friday.

Application/Control Number: 10/614,368 Page 4

Art Unit: 2824

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms can be reached on (571) 272-1869. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BKS